

	Hit s	Search Text	DBs
43	1	((heat\$4 or anneal\$4 or bak\$4) same (top or upper or front) same (bottom or lower or (substrate near5 holder) or hold\$4 or stage) same (resist or photoresist) same (reflow\$4 or (glass near9 transit\$5)) same (substrate or wafer) same pressure) and develop\$4 and ((coat\$4 or form\$4) same (resist or photoresist)) and (exposure or irradiat\$))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
44	61	((heat\$4 or anneal\$4 or bak\$4) same (top or upper or front) same (bottom or lower or (substrate near5 holder) or hold\$4 or stage) same (resist or photoresist) same (reflow\$4 or (glass near9 transit\$5)) same (substrate or wafer)) and develop\$4 and ((coat\$4 or form\$4) same (resist or photoresist)) and (exposure or irradiat\$))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
45	1	((heat\$4 or anneal\$4 or bak\$4) same (top or upper or front) same (bottom or lower or (substrate near5 holder) or hold\$4 or stage) same (resist or photoresist) same (reflow\$4 or (glass near9 transit\$5)) same (substrate or wafer)) and develop\$4 and ((coat\$4 or form\$4) same (resist or photoresist)) and (exposure or irradiat\$)) and ((heat\$4 or bak\$4 or anneal\$4 or PEB or (post near9 bak\$4)) same (substrate or wafer or workpiece) same (photoresist or resist or photocur\$4 or polyimide) same pressure same control\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB